IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

pplicants:

Yeo, et al.

Attorney Docket: TSM03-0421

Filed:

June 27, 2003

Examiner:

TBD

Serial No.:

10/608,287

Art Unit:

2812

For:

Structure and Method for Forming the Gate Electrode in a Multiple-Gate Transistor

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO-1449 that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits.

Respectfully submitted,

Ira S. Matsil

Attorney for Applicant

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PTO/SB/08A (02-03)
Approved for use through 4/30/2003. OMB 0651-0031
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Compl te if Kn wn Substitute for form 1449/PTO Application Number 10/608.287 June 27, 2003 Filing Date INFORMATION DISCLOSURE First Named Inventor Yeo, et al. STATEMENT BY APPLICANT Art Unit 2812 (use as many sheets as necessary) TBD **Examiner Name** TSM03-0421 Attorney Docket Number of 1 Sheet

U.S. PATENT DOCUMENTS					
Examiner Initlals*	Cite No.1	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevan Figures Appear
	Α	US-6,252,284 B1	06-26-2001	Muller, et al.	
	В	US ₂ 6,391,695 B1	05-21-2002	Yu	
	C	U\$-6,391,782 B1	05-21-2002	Yu	
•###	D	US-6,413,802 B1	07-02-2002	Hu, et al.	
***************************************	E	US-6,432,829 B2	08-13-2002	Muller, et al.	
	F	US-6,451,656 B1	09-17-2002	Yu, et al.	
	G	US-6,492,212 B1	12-10-2002	leong, et al.	
	Н	US-2003/0067017 A1	04-10-2003	leong, et al.	
	11	US-2003-0102497 A1	06-05-2003	Fried, et al.	
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	FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Foreign Patent Document Country Code ³ - Number ⁴ - Kind Code ⁵ (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T⁵
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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2 of Sheet

Compl te if Known			
Application Number	10/608,287		
Filing Date	June 27, 2003		
First Named Inventor	Yeo, et al.		
Group Art Unit	2812		
Examiner Name	TBD		
Attorney Docket Number	TSM03-0421		

	OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS			
	Π	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the	₇ 2	
Examiner	Cite	item (book, magazina, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue		
Initials*	No.	number(s), publisher, city and/or country where published.		
	J	HUANG, X., et al. "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5 (May 2001) pp. 880-886.		
	К	YANG, FL., et al. "35nm CMOS FinFETs," 2002 Symposium on VLSI Technology Digest of Technical Papers, (June 2002) pp. 109-110.		
	J	WONG, HS.P. "Beyond the Conventional Transistor," IBM Journal of Research and Development, Vol. 46, No. 2/3 (March/May 2002) pp. 133-167.		
- WAS COLUMN TO A STATE OF THE	L	CHAU, R., et al. "Advanced Depleted-Substrate Transistors: Single-gate, Double-Gate and Tri-Gate," Extended Abstracts of the 2002 International Conference on Solid State Devices and Materials, (2002) pp. 68-69.		
	М	YANG, FL., et al. "25nm CMOS Omega FETs," International Electron Devices Meeting, Digest of Technical Papers, (December 2002) pp. 255-258.		
	N	COLINGE, J.P., et al. "Silicon-On-Insulator 'Gate -All-Around Device," International Electron Devices Meeting, (1990) pp. 595-598.		
	0	LEOBANDUNG, E., et al., "Wire-Channel and Wrap-Around-Gate Metal-Oxide-Semiconductor Field-Effect Transistors with a Significant Reduction of Short Channel Effects," Journal of Vacuum Science and Technology, Vol. B 15, No. 6, (November/December 1997) pp. 2791-2794.		
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